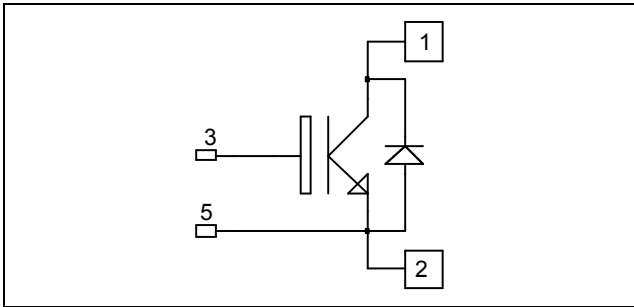


**Single switch  
Trench + Field Stop IGBT4  
Power Module**

**$V_{CES} = 1200V$   
 $I_C = 700A @ T_c = 80^\circ C$**



### Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

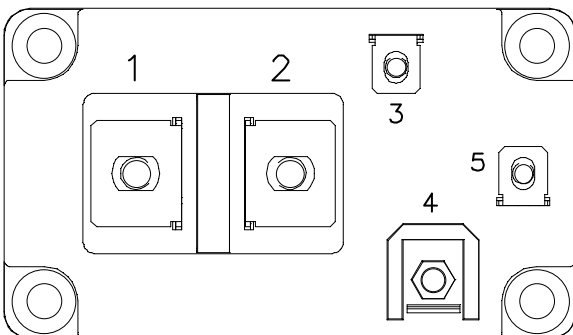
### Features

- Trench + Field Stop IGBT 4 Technology
  - Low voltage drop
  - Low leakage current
  - Low switching losses
  - Soft recovery parallel diodes
  - Low diode VF
  - RBSOA and SCSOA rated

- Kelvin emitter for easy drive
- M6 connectors for power
- M4 connectors for signal
- High level of integration

### Benefits

- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive  $T_C$  of  $V_{CESat}$
- RoHS Compliant



### Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
$V_{CES}$	Collector - Emitter Breakdown Voltage	1200	V
$I_C$	Continuous Collector Current	$T_C = 25^\circ C$	910
		$T_C = 80^\circ C$	700
$I_{CM}$	Pulsed Collector Current	$T_C = 25^\circ C$	1800
$V_{GE}$	Gate - Emitter Voltage	$\pm 20$	V
$P_D$	Maximum Power Dissipation	$T_C = 25^\circ C$	3000
RBSOA	Reverse Bias Safe Operating Area	$T_j = 125^\circ C$	1200A@1150V

**CAUTION:** These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on [www.microsemi.com](http://www.microsemi.com)

All ratings @  $T_j = 25^\circ\text{C}$  unless otherwise specified

**Electrical Characteristics**

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$I_{CES}$	Zero Gate Voltage Collector Current	$V_{GE} = 0V$ ; $V_{CE} = 1200V$			4	mA
$V_{CE(sat)}$	Collector Emitter Saturation Voltage	$V_{GE} = 15V$ $I_C = 600A$		1.8 2.2	2.2	V
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}$ , $I_C = 24\text{ mA}$	5	5.8	6.5	V

**Dynamic Characteristics**

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$C_{ies}$	Input Capacitance	$V_{GE} = 0V$ $V_{CE} = 25V$ $f = 1\text{MHz}$		37.2		nF
$C_{oes}$	Output Capacitance			2.3		
$C_{res}$	Reverse Transfer Capacitance			2.04		
$Q_G$	Gate charge	$V_{GE} = -8V / 15V$ ; $V_{CE} = 600V$ $I_C = 600A$		3.4		$\mu\text{C}$
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching ( $25^\circ\text{C}$ ) $V_{GE} = \pm 15V$ $V_{CE} = 600V$ $I_C = 600A$ $R_G = 1.8\Omega$		160		ns
$T_r$	Rise Time			30		
$T_{d(off)}$	Turn-off Delay Time			340		
$T_f$	Fall Time			80		
$T_{d(on)}$	Turn-on Delay Time		Inductive Switching ( $150^\circ\text{C}$ ) $V_{GE} = \pm 15V$ $V_{CE} = 600V$ $I_C = 600A$ $R_G = 1.8\Omega$		170	
$T_r$	Rise Time			40		
$T_{d(off)}$	Turn-off Delay Time			450		
$T_f$	Fall Time			170		
$E_{on}$	Turn-on Switching Energy	$V_{GE} = \pm 15V$ $V_{CE} = 600V$ $I_C = 600A$			66	
$E_{off}$	Turn-off Switching Energy	$R_G = 1.8\Omega$		66		mJ
$I_{sc}$	Short Circuit data	$V_{GE} \leq 15V$ ; $V_{Bus} = 900V$ $t_p \leq 10\mu\text{s}$ ; $T_j = 150^\circ\text{C}$		2400		A

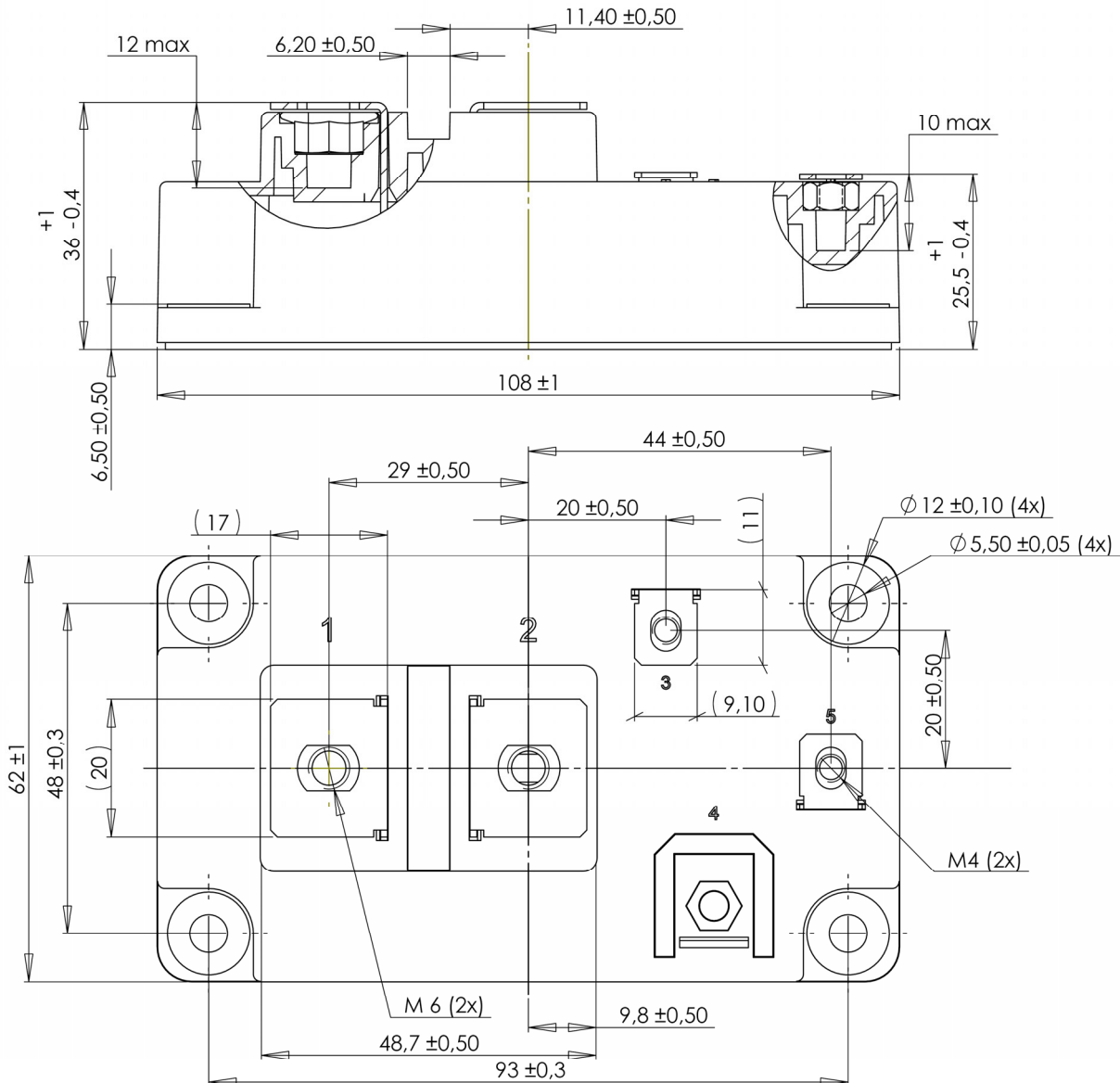
**Diode ratings and characteristics**

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit	
$V_{RRM}$	Maximum Repetitive Reverse Voltage		1200			V	
$I_{RRM}$	Maximum Reverse Leakage Current	$V_R = 1200V$			250 2000	$\mu\text{A}$	
$I_F$	DC Forward Current			600		A	
$V_F$	Diode Forward Voltage	$I_F = 600A$ $V_{GE} = 0V$		1.7 1.65	2.2	V	
$t_{rr}$	Reverse Recovery Time	$I_F = 600A$ $V_R = 600V$ $di/dt = 7000A/\mu\text{s}$		155 300		ns	
$Q_{rr}$	Reverse Recovery Charge			53 110			$\mu\text{C}$
$E_{rr}$	Reverse Recovery Energy			23.5 46		mJ	

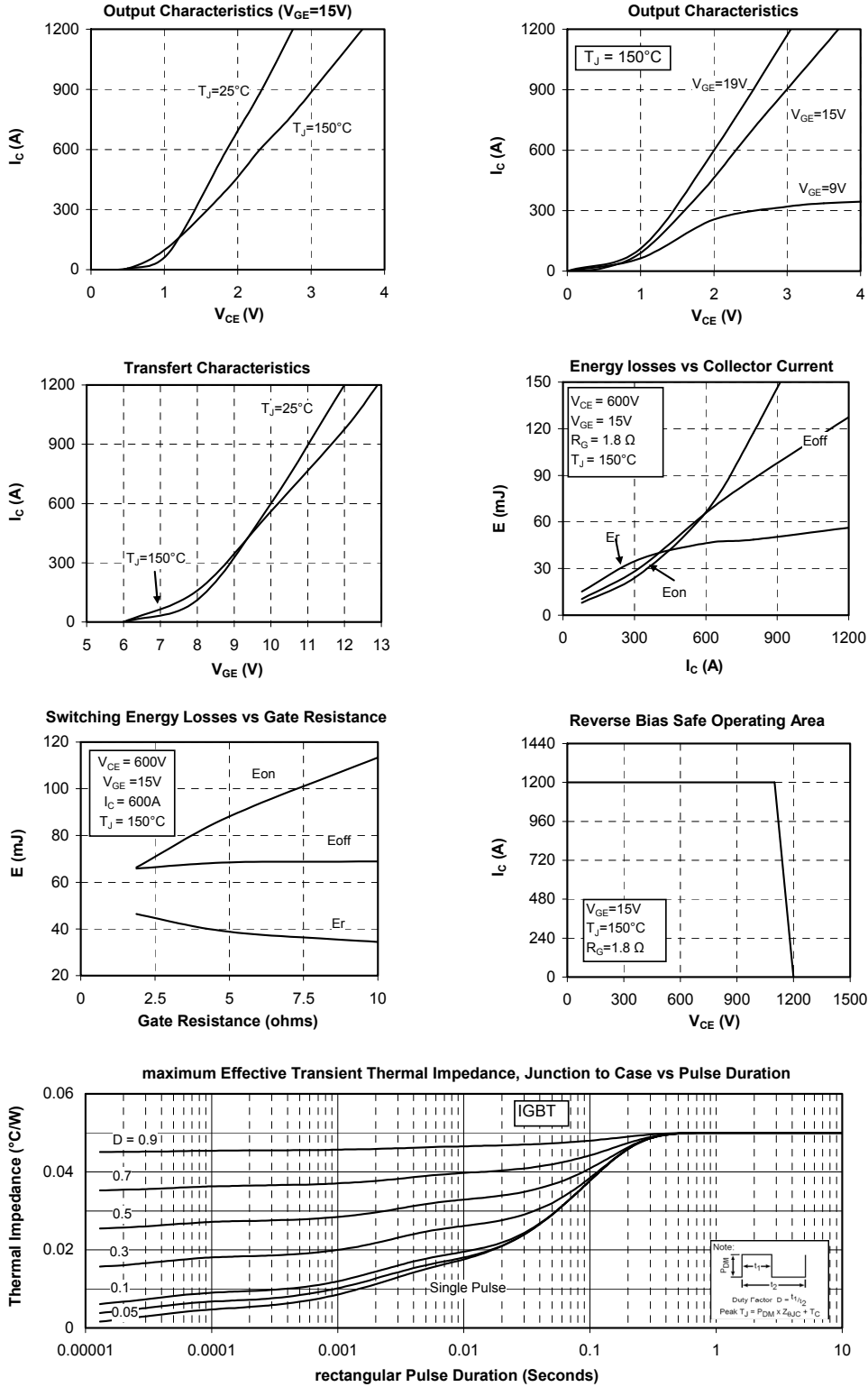
### Thermal and package characteristics

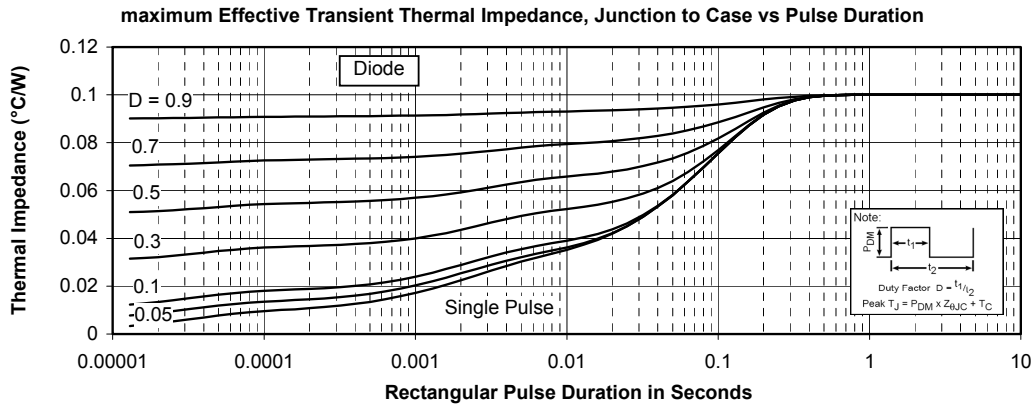
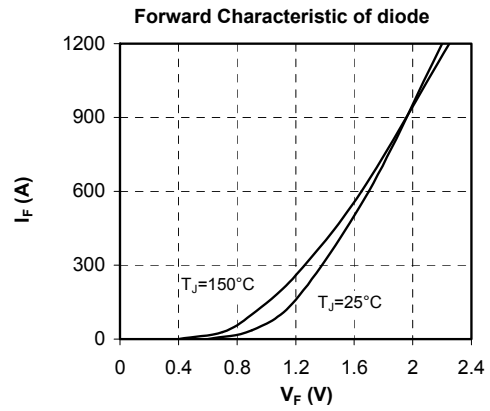
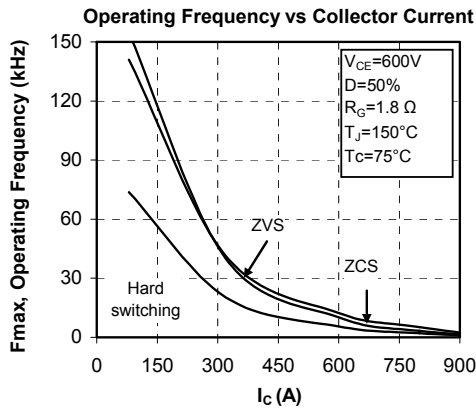
Symbol	Characteristic	Min	Typ	Max	Unit
R <sub>thJC</sub>	Junction to Case Thermal Resistance	IGBT		0.05	°C/W
		Diode		0.1	
V <sub>ISOL</sub>	RMS Isolation Voltage, any terminal to case t=1 min, 50/60Hz	4000			V
T <sub>J</sub>	Operating junction temperature range	-40		175	°C
T <sub>STG</sub>	Storage Temperature Range	-40		125	
T <sub>C</sub>	Operating Case Temperature	-40		125	
Torque	Mounting torque	M6	3	5	N.m
		M4	1	2	
Wt	Package Weight			350	g

### D4 Package outline (dimensions in mm)



## Typical Performance Curve





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